

### Silicon Power Diode

**PSM/PSMR 200K**  
**PSMF/PSMFR 200K**

$I_{F(AV)} = 200 \text{ A}$   
 $V_{RRM} = 100 - 1000 \text{ V}$

Preliminary Data Sheet

$V_{RRM}$ max. repetitive peak voltage (V)	$V_{R(RMS)}$ max. RMS reverse voltage (V)	$V_R$ max. DC blocking voltage (V)	recommended RMS working voltage (V)	Type
100	70	100	40	PSM/PSMR 200/01K
200	140	200	80	PSM/PSMR 200/02K
400	280	400	160	PSM/PSMR 200/04K
600	420	600	240	PSM/PSMR 200/06K
800	560	800	320	PSM/PSMR 200/08K
1000	700	1000	400	PSM/PSMR 200/10K

with terminal lead

PSMF/PSMFR 200/01K
PSMF/PSMFR 200/02K
PSMF/PSMFR 200/04K
PSMF/PSMFR 200/06K
PSMF/PSMFR 200/08K
PSMF/PSMFR 200/10K

Symbol	Conditions	Maximum Ratings
$I_{F(AV)}$	$T_C = 130^\circ\text{C}$	200 A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$	4300 A
$I_{FRM}$	max. peak cycle repetitive surge current	1100 A
$I^2t$	max. $I^2t$ rating (non-rep.) for 5 to 10 ms	92500 A <sup>2</sup> s
$I_{R(AV)}$	max. average reverse leakage current at $V_{RRM}$ ; $T_C = 25^\circ\text{C}$	min. 30 $\mu\text{A}$ max. 50 $\mu\text{A}$
$V_{FM}$	max. peak forward voltage drop @ rated $I_{F(AV)}$	1.35 V
$R_{thJC}$	max. thermal resistance junction to case	0.2 K/W
$T_{VJ}$	operating junction temperature	-65... + 150 $^\circ\text{C}$
$T_{VJM}$	max. virtual junction temperature	150 $^\circ\text{C}$
$T_{stg}$	storage temperature	-65... + 200 $^\circ\text{C}$
$M_d$	mounting torque (non-lubricated threads)	min. 2.0 mkg max. 3.0 mkg
Weight	typ.	150 g

#### Features

- Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available in Avalanche Characteristic

